

Product Change Notice (PCN)

Subject: Design Change for Listed Intersil Products

Publication Date: 4/21/2015

Effective Date: 7/21/2015

Revision Description:

Initial Release

Description of Change:

This notice is to advise our customers of a minor silicon design revision.

Reason for Change:

Three minor changes have been made to the design to improve manufacturability of the product while maintaining product functionality to specified requirements.

1. Small change to current sense amplifier compensation network for better current sense performance.
2. Removal of a Schottky diode on the ISENA pin to improve ISENSE accuracy under certain DCR applications
3. Update of ESD structure between BST and VR to eliminate the potential to introduce switching noise into the current sense measurement

These changes have been made to improve product robustness without impact to circuit performance.

Impact on fit, form, function, quality & reliability:

The change will have no impact on the form, fit, function, quality, reliability and environmental compliance of the devices.

Product Identification:

There will be no change in the external marking of the packaged parts or to the product data sheet electrical specification. Product affected by this change is identifiable via Intersil's internal traceability system.

Qualification status: Complete, see attached

Sample availability: 6/30/2015

Device material declaration: Available upon request

Questions or requests pertaining to this change notice, including additional data or samples, must be sent to Intersil within 30 days of the publication date.

For additional information regarding this notice, please contact your regional change coordinator (below)			
Americas: PCN-US@INTERSIL.COM	Europe: PCN-EU@INTERSIL.COM	Japan: PCN-JP@INTERSIL.COM	Asia Pac: PCN-APAC@INTERSIL.COM

Appendix A - Affected Products List (see attached)

Appendix B - Qualification Results (see attached)

Appendix A:

ZL2005ALPF-03	ZL6102ALAF TK	ZL6105ALBFTKR5554	ZL6100ALAF T
ZL2005ALPFT-03	ZL6102ALAF TKR5529	ZL9006MAIRZ	ZL6100ALAF TK
ZL2005ALPFTK-03	ZL6105ALAF TK-02	ZL9006MAIRZ-T	ZL6100ALAF TS2705
ZL2005PALRFT	ZL6105ALAF TKR5546	ZL9010MAIRZ	ZL6102ALBF
ZL2005PALRFT1	ZL6105ALAF TKR5549	ZL9010MAIRZ-T	ZL6102ALBF TK
ZL2005PALRFT1R5540	ZL6105ALAF TKR5553	ZLS1003ALAF TK	ZL6102ALCF
ZL2006ALNF	ZL6105ALAF TKR5554	ZL2005ALNF	ZL6102ALCF TK
ZL2006ALNFB	ZL6105ALAF TKR5619	ZL2005ALNFT	ZL6105ALAF
ZL2008EALAF T	ZL6105ALAF TKR5638	ZL2005ALNFT1	ZL6105ALAF T
ZL2008EALAF T1	ZL6105ALAF TKR5639	ZL2005ALNFT1S2568	ZL6105ALAF TK
ZL2008EALAF T1R5540	ZL6105ALAF TKR5646	ZL2006ALNFT	ZL9006MIRZ
ZL2008EALAF T1R5558	ZL6105ALAF TKR5649	ZL2006ALNFT1	ZL9006MIRZ-T
ZL6100ALBF	ZL6105ALAF TKR5653	ZL2008ALBF T	ZL9010MIRZ
ZL6100ALBF TK	ZL6105ALAF TKS2768	ZL2008ALBF T1	ZL9010MIRZ-T
ZL6102ALAF	ZL6105ALAF TR5546	ZL2008ALBF T1S2568	ZLS1002ALAF TK

Appendix B:

Qualification Results				
Stress	Test Method	Sample Size	# of Lots	Result
High Temperature Operating Life (HTOL)	JESD22-A108	76	1	Pass
Unbiased HAST (UHAST)	JESD22-A118	81	1	Pass, QBE
Temperature Cycle (TC)	JESD22-A104	81	1	Pass QBE
ESD - Human Body Model (HBM)	JESD22-A114	3	1	2kv
ESD - Charged Device Model (CDM)	JESD22-C101	3	1	750v
ESD - Machine Model (MM)	JESD22-A115	3	1	200v
Latch-up (LU)	JESD78	6	1	Pass